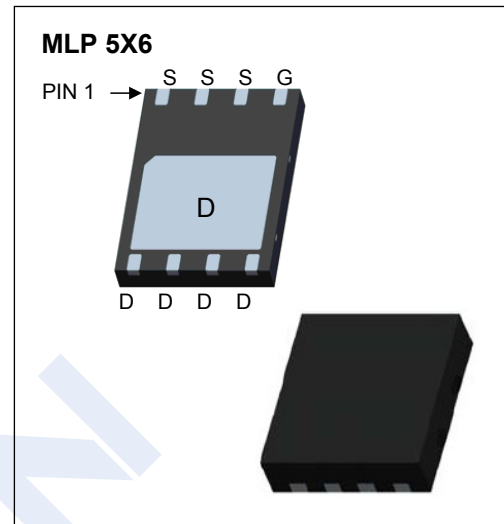
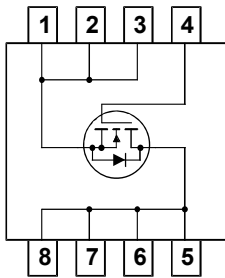


N-Channel MOSFET

FDMS2572 (KDMS2572)

■ Features

- $V_{DS} (V) = 150V$
- $I_D = 4.5 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 47m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 53m\Omega$ ($V_{GS} = 6V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	(Note.1)	I_D	4.5	A
Pulsed Drain Current		I_{DM}	30	
Drain-Source Avalanche Current		I_{AR}	15	
Power Dissipation	(Note.1)	P_D	2.8	W
	(Note.2)		1.1	
Thermal Resistance.Junction- to-Ambient	(Note.1)	R_{thJA}	44	$^\circ C/W$
	(Note.2)		115	
Junction Temperature		T_J	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55 to 150	

Note.1: $44^\circ C/W$ when mounted on a $1in^2$ pad of 2 oz copper

Note.2: $115^\circ C/W$ when mounted on a minimum pad of 2 oz copper

N-Channel MOSFET

FDMS2572 (KDMS2572)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	150			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μA	2		4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =4.5A			47	mΩ
		V _{GS} =10V, I _D =4.5A, T _J =125°C			103	
		V _{GS} =6V, I _D =4.5A			53	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =4.5A		14		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =75V, f=1MHz		1960		pF
Output Capacitance	C _{oss}			130		
Reverse Transfer Capacitance	C _{rss}			30		
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.3		Ω
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =75V, I _D =4.5A		31	43	nC
Gate Source Charge	Q _{gs}			9		
Gate Drain Charge	Q _{gd}			7		
Turn-On DelayTime	t _{d(on)}	V _{DD} = 75 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		11	20	ns
Turn-On Rise Time	t _r			8	16	
Turn-Off DelayTime	t _{d(off)}			38	61	
Turn-Off Fall Time	t _f			31	50	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 4.5A, di/dt= 100A/μs		67		nC
Body Diode Reverse Recovery Charge	Q _{rr}			130		
Single Pulse Drain-Source Avalanche Energy	E _{AS}	V _{DD} = 75 V, I _D = 15 A, L=1mH			112	mJ
Diode Forward Voltage	V _{SD}	I _S =2.2A, V _{GS} =0V			1	V

Note : Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

■ Marking

Marking	FDMS2572
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N-Channel MOSFET

FDMS2572 (KDMS2572)

■ Typical Characteristics

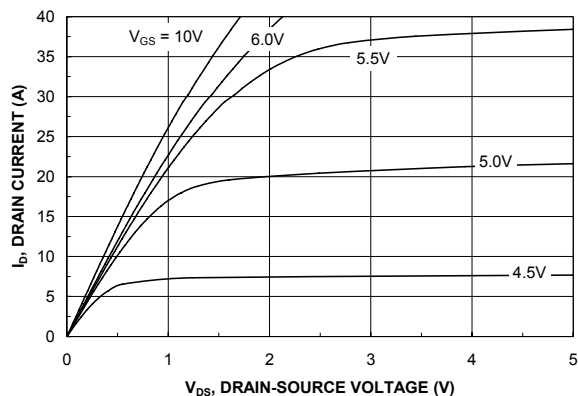


Figure 1. On-Region Characteristics.

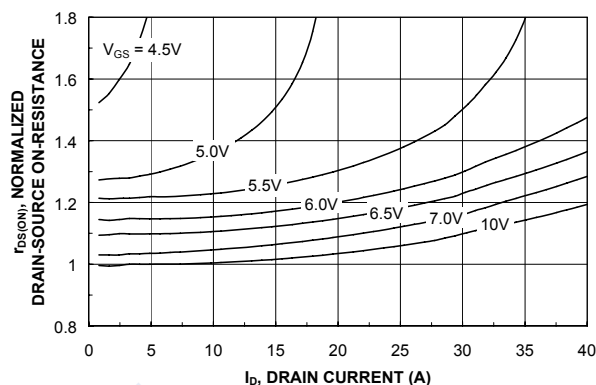


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

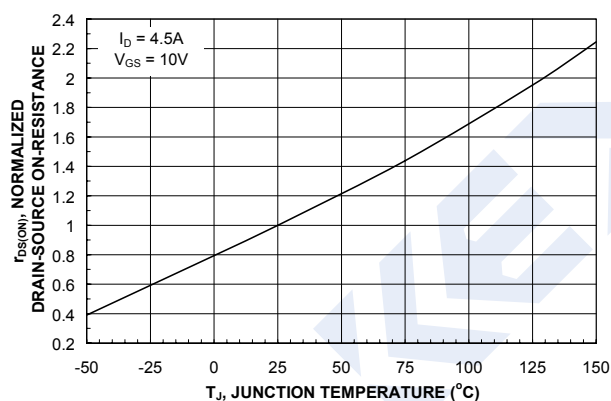


Figure 3. On-Resistance Variation with Temperature.

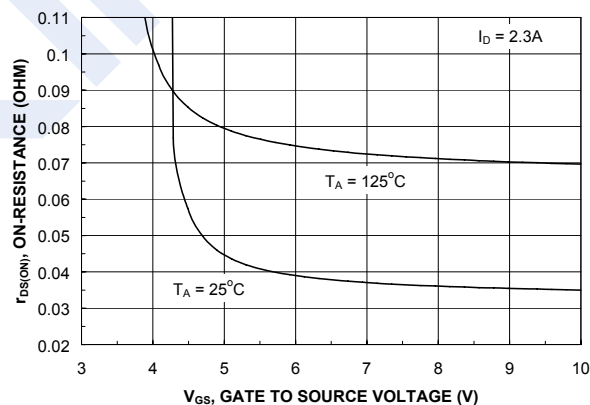


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

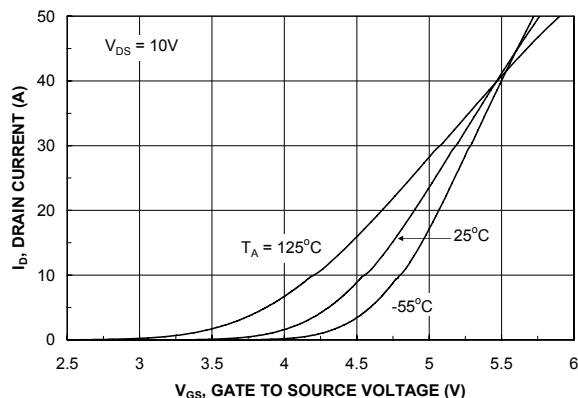


Figure 5. Transfer Characteristics.

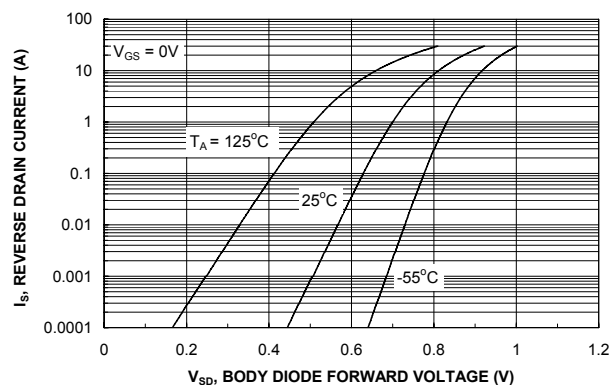


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

N-Channel MOSFET

FDMS2572 (KDMS2572)

Typical Characteristics

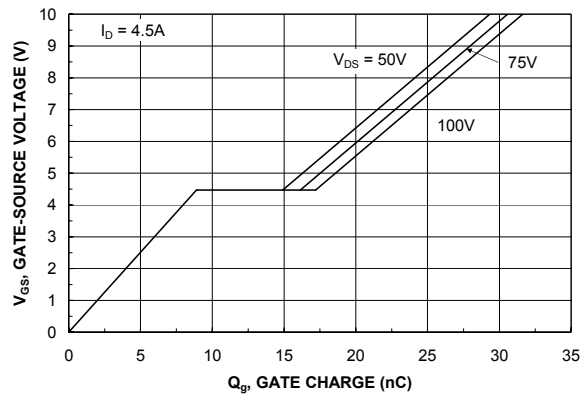


Figure 7. Gate Charge Characteristics.

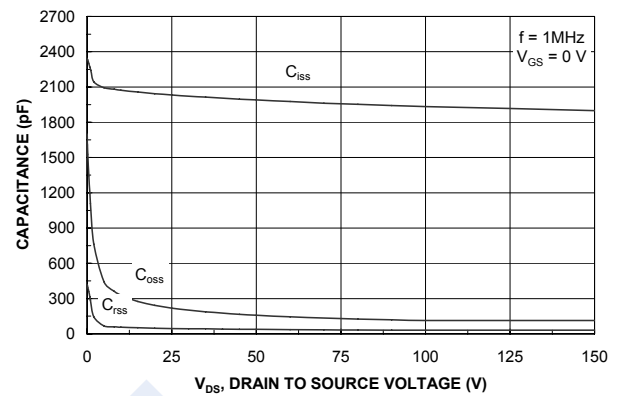


Figure 8. Capacitance Characteristics.

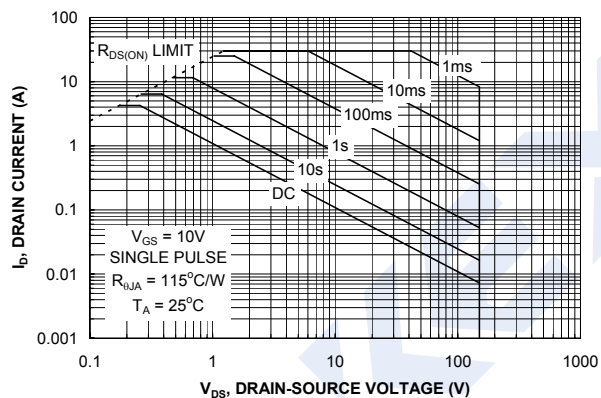


Figure 9. Maximum Safe Operating Area.

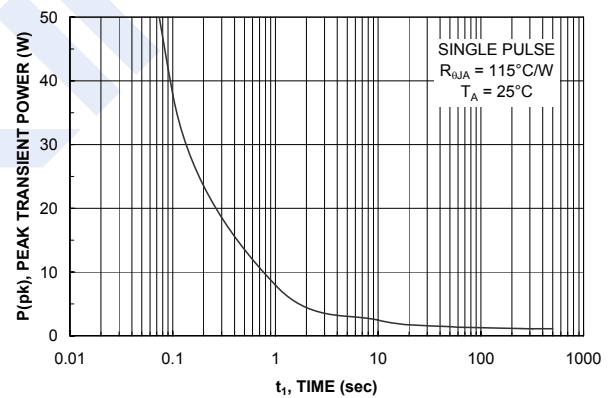


Figure 10. Single Pulse Maximum Power Dissipation.

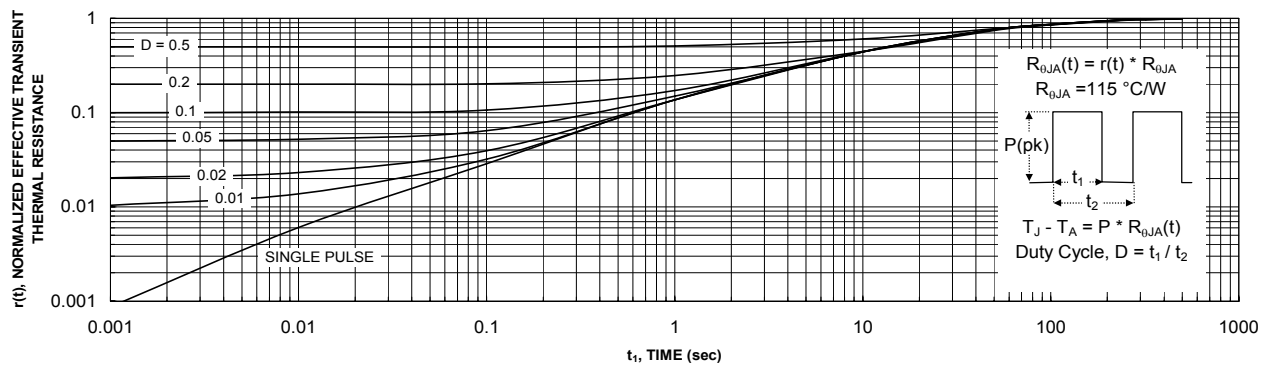


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

Dimensional Outline and Pad Lay-out

MLP 5X6

Unit:mm

